

NPN RF POWER TRANSISTOR

DESCRIPTION

The **ASI SRF 1318** is a Common Emitter Device Designed for Class C Amplifier Applications up to 1 GHz.

FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	1.7 A
V_{CB0}	36 V
P_{DISS}	15 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	12 °C/W

PACKAGE STYLE 280 4L STUDLESS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25.65	1.055/26.80
B	.220/5.59	.230/5.84
C	.270/6.86	.285/7.24
D	.003/0.08	.007/0.18
E	.117/2.97	.137/3.48
F	.5/2/14.53	
G	.130/3.30	
H	.275/6.99	.285/7.24
I	.640/16.26	
J	.175/4.45	.21/75.51

1 = Collector
3 = Base 2 & 4 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 10 mA	36			V
BV_{CEO}	I _C = 50 mA	16			V
BV_{EBO}	I _E = 2.0 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 200 mA	20			---
C_{OB}	V _{CB} = 12.5 V f = 1.0 MHz		19		pF
*P_G					dB
*η_C					%

* RF SPECIFICATIONS ARE CONTROLLED BY CUSTOMER DRAWING AND ARE PROPRIETARY.